BET-C202
ELECTRONIC DEVICES

MM: 100 **Sessional: 30**
Time: 3 hrs **ESE: 70**
L T P **Credits 4**
3 1 0

NOTE: The question paper shall consist of three sections (Sec.-A, Sec.-B and Sec.-C). Sec.-A shall contain 10 objective type questions of one mark each and student shall be required to attempt all questions. Sec.-B shall contain 10 short answer type questions of four marks each and student shall be required to attempt any five questions. Sec.-C shall contain 8 descriptive type questions of ten marks each and student shall be required to attempt any four questions. Questions shall be uniformly distributed from the entire syllabus. The previous year paper/model paper can be used as a guideline and the following syllabus should be strictly followed while setting the question paper.

UNIT I

Semiconductors, energy band description of semiconductors, effect of temperature on semiconductors, intrinsic and extrinsic semiconductors, donor and acceptor impurities, electron and hole concentration, conductivity of a semiconductor, mobility and resistivity, Generation and Recombination, Hall effect, Fermi level, mass action law, charge densities in a semiconductor, diffusion and Poisson and continuity equation.

UNIT II

P-N junction and its properties, V-I characteristics of P-N junction, semiconductor-diode, depletion layer, equivalent circuits of junction diode, diode equation, diode resistance and capacitance, application of junction diode as clippers, clampers and rectifiers (Half-wave, Full-wave and bridge), efficiency of rectifiers, ripple factor, filter circuits, Zener and avalanche breakdown mechanism, Zener diode and its characteristics, equivalent circuit of Zener diode, Zener diode as a voltage regulator, LED, photo diode and solar cell.

UNIT III

Bipolar junction transistor (BJT) and its action, Transistor configurations (CB, CE and CC) and their characteristics, cut-off, active and saturation regions. Transistor as a switch, operating point, dc load line, Transistor biasing and its necessity, thermal runaway, types of biasing and their analysis, stability factors, Transistor as a regulator. Concept of Transistor amplifier, graphical analysis of CE amplifier, dc and ac equivalent circuits, Emitter follower and its ac model.

UNIT IV

Ebers-Moll model of BJT, T model of BJT, Hybrid model of BJT at low frequency, computation of voltage gain, current gain and power gain, Zi and Zo and approximate formulas, high frequency transistor hybrid π model.

UNIT V

Field Effect Transistor: JFET and its characteristics, biasing of JFET, small signal low frequency and high frequency model of JFET amplifier, configurations of JFET, MOSFET, MESFET (Enhancement & depletion types) their construction and characteristics, configuration of MOSFET, MOS capacitor.

Text Book

1. Integrated Electronics: Jacob Millman & C.C. Halkias

References

1. Malvino and leach “Digital principle and applications.
2. Streetman Ben.G, “Solid state electronic devices” (3/e), PHI
3. Millman and grabel, “Microelectronics” PHI
4. Robert Bolyestad “Electronic devices and circuit”, PHI